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ATTY. D KET NO. 79329

SERIAL NO. 09/137,084

APPLICANT

Stumborg, Michael F. et al. FILING DATE GROUP

08/20/98

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REFERENCE DESIGNATION U.S. PATENT DOCUMENTS									
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
Va)	AA	4,502,209	3/5/85	Eizenberg et al.	29	589	-		
	AB	4,965,656	10/23/90	Koubuchi et al.	357	71	-		
	AC	5,389,575	2/14/95	Chin et al.	437	190	_		
•	AD	5,489,548	2/6/96	Niskioka et al.	437	60	-		
	ΑE	5,547,901	8/20/96	Kim et al.	437	187	-		
	AF	5,552,341	9/3/96	Lee	437	192	_		
	AG	5,554,254	9/10/96	Huang et al.	156	625.1	_		
	AH	5,624,874	4/29/97	Lim et al.	438	653	_		
	AI	5,637,533	6/10/97	Choi	438	643	_		
	AJ	5,668,054	9/16/97	Sun et al.	438	653			
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(Information Disclosure Statement - Section 9 PTO-1449 (Modified) [6-1] page 01 of 03)

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APPLICANT

Stumborg, Michael F. et al.

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(Information Disclosure Statement - Section 9 PTO-1449 (Modified) [6-1] page 02 of 03)

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Vn.	4,291,327	9/22/81	Tsang	357	52		
	4,550,331	10/29/85	Milano	357	24		
	4,692,993	9/15/87	Clark et al.	437	53		
	4,847,666	7/11/89	Heremans et al.	357	16		
	5,124,762	6/23/92	Childs et al.	357	16		
	5,435,264	7/25/95	Santiago et al.	117	92		
	5,391,517	2/21/95	Gelatos et al.	437	190	11_	
Vn	5,773,359	6/30/98	Mitchell et al.	438	614		
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√u_	2-266569	10/31/90	Japan			Abstract	
	OTHER DOCUM	IENTS (Includin	g Author, Title, Date, Pe	rtinent Pag	es, Etc.)		
7.	S.M. Sze, "Semicond	uctor Devices Ph	ysics and Technology",	1985, pp. 2	08-210.		
<u>V.</u>			/(Ga,In)(As,Sb) Structur			Growth, Vol. 8	B1
Ñ	Clemens, et al., "Grov No. 4, 15 Aug. 1989,	wth of BaF <sub>2</sub> and pp. 1680-1685.	of BaF <sub>2</sub> /SrF <sub>2</sub> layers on (0	001) oriente	ed GaAs", J.	Appl. Phys., V	Vol. 66,
Vz	Hung, et al., " Epitax without in situ cleani	ial growth of alkang", Appl. Phys.	aline earth fluoride films Lett., Vol. 60, No. 2, 13	on HF-trea Jan. 1992,	ated Si and (N pp. 201-203.	NH <sub>4</sub> ) <sub>2</sub> S <sub>x</sub> -treate	ed GaAs
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Vn	5,695,810	12/9/97	Dubin et al.	427	96	-			
y de	5,824,599	10/20/98	Schacham-Diamand, et al.	437	230				
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Vn	Chaudhari, et al., "Calcium Fluoride thin films on GaAs (100) for possible metal-insulator-semiconductor applications", Appl. Phys. lett., Vol. 62, No. 8, 22 Feb. 1993, pp. 852-854.								
	Colbow, et al., "Photoemission study of the formation of SrF <sub>2</sub> /GaAs(100) and BaF <sub>2</sub> /GaAs(100) interfaces", Physical Review B, Vol. 49, No. 3, 15 Jan. 1994, pp. 1750-1756.								
		Chu, et al., "The Role of Barium in the Heteroepitaxial Growth of Insulator and Semiconductors on Silicon", Mat. Res. Symp. Proc., Vol. 334, 1994, pp. 501-506.							
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	GaAs by x-ray photoele	arsenide", J. Appl. Phys., Vol. 77, No. 6, 15 March 1995, pp. 2739-2744.  Stumborg, et al., "Surface chemical state populations in the molecular beam epitaxy deposition of BaF <sub>2</sub> on GaAs by x-ray photoelectron spectroscopy and heavy-ion backscattering spectroscopy", J. Vac. Sci. Technol., Vol. 14, No. 1, Jan./Feb. 1996, pp. 69-79.							
√ <u>~</u>	Chu, et al., "Heteroepit Vol. B47, 1997, pp. 22	-	of Group IIa fluorides or	n gallium a	rsenide", Ma	at. Sci. and Eng. B,			
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Va.	4,550,331	10/29/85	Milano	357	24		
Vu	4,692,993	9/15/87	Clark et al.	437	53	<u> </u>	
Vin	4,847,666	7/11/89	Heremans et al.	357	16		
Vn	5,124,762	6/23/92	Childs et al.	357	16		
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√ <u>n</u>	Truscott, et al., "MBI (1987), pp. 552-556.	E growth of Ba	F <sub>2</sub> /(Ga,In)(As,Sb) Struct	ures", Journa	l of Crysta	l Growth, Vol. 81	
V <u>~</u>	No. 4, 15 Aug. 1989,	, pp. 1680-1685	d of BaF <sub>2</sub> /SrF <sub>2</sub> layers on				
No	Unng et al "Enitay	rial growth of a	lkaline earth fluoride films. Lett., Vol. 60, No. 2, 1	ns on HF-tre 3 Jan. 1992,	ated Si and pp. 201-20	$(NH_4)_2 S_x$ -treated GaAs 33.	
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Va		5,824,599	10/20/98	Schacham-Diamand, et al.	437	230			
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<u> </u>		Chaudhari, et al., "Calcium Fluoride thin films on GaAs (100) for possible metal-insulator-semiconductor applications", Appl. Phys. lett., Vol. 62, No. 8, 22 Feb. 1993, pp. 852-854.							
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<u>v</u>		Chu, et al., "The Role of Mat. Res. Symp. Proc.,		Heteroepitaxial Growth , pp. 501-506.	of Insulato	r and Semic	onductors on Silicon",		
Vh.		Stumborg, et al., "Dete dependence of RBS yie	rmination of greelds", Nucl. Inst	owth mechanisms of MB r. and Methods in Physic	E grown Bass Res. B, V	aF <sub>2</sub> on Si(10) Vol. 95, 1995	0) by target angle , pp. 319-322.		
<u> </u>				ial chemistry of insulatin 6, 15 March 1995, pp. 2		ium fluoride	on gallium		
Ţ		Stumborg, et al., "Surf GaAs by x-ray photoel Vol. 14, No. 1, Jan./Fe	ectron spectros	ate populations in the molecopy and heavy-ion backs	lecular bear scattering s	m epitaxy de pectroscopy'	position of BaF <sub>2</sub> on ', J. Vac. Sci. Technol.,		
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Serial No. Atty. Docket No. Form PTO-1449 U.S. Department of Commerce Patent & Trademark Office (Rev. 2-32) 09/137,084 NC79329 Applicant' INFORMATION DISCLOSURE STATEMENT STUMBORG ET AL. (Use several sheets if necessary) Group Filing Date NOV - 1 1999 8/20/98 2811 >, ,u,s-patent documents Filing Date Class Sub-Name **Document Number** Date Examiner (if appropriate) Class **Initial** 612 7/1993 McKee, et al. 156 5,225,031 AA 9/1993 Morar et al. 437 196 5,248,633 AB 257 213 1/1995 Nakamura AC 5,378,905 1/1996 McKee et al. 117 108 ΑD 5,482,003 505 235 1/1997 Himpsel ΑE 5,593,951 117 106 5/1998 Cho 5,753,040 ΑF FOREIGN PATENT DOCUMENTS Translation Sub-Yes/No Class class Date Country Document OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) DATE CONSIDERED EXAMINER 00/15/100 HUNG K. VU Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include EXAMINER: copy of this form with next communication.

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